



2SB775/2SD895

85V/6A, AF 35W Output Applications

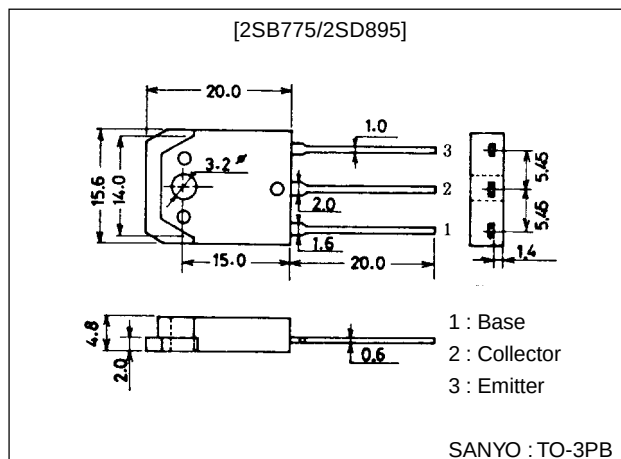
Features

- Wide ASO because of on-chip ballast resistance.
- Capable of being mounted easily because of one-point fixing type plastic molded package (Interchangeable with TO-3).
- Large current capacity : $I_C=6A$
- Highly resistance breakdown due to wide ASO.

Package Dimensions

unit:mm

2022A



() : 2SB775

Specifications

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(-)100	V
Collector-to-Emitter Voltage	V_{CEO}		(-)85	V
Emitter-to-Base Voltage	V_{EBO}		(-)6	V
Collector Current	I_C		(-)6	A
Collector Current (Pulse)	I_{CP}		(-)10	A
Collector Dissipation	P_C	$T_c=25^\circ C$	60	W
Junction Temperature	T_J		150	$^\circ C$
Storage Temperature	T_{stg}		-40 to +150	$^\circ C$

Electrical Characteristics at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)40V, I_E=0$			(-)0.1	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)4V, I_C=0$			(-)0.1	mA
DC Current Gain	h_{FE1}	$V_{CE}=(-)5V, I_C=(-)1A$	60*		200*	
	h_{FE2}	$V_{CE}=(-)5V, I_C=(-)3A$	20			
Gain-Bandwidth Product	f_T	$V_{CE}=(-)5V, I_C=(-)1A$		(18)15		MHz
Output Capacitance	C_{ob}	$V_{CB}=(-)10V, f=1MHz$		160		pF
Base-to-Emitter Voltage	V_{BE}	$V_{CE}=(-)5V, I_C=(-)1A$			(-)1.5	V
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)4A, I_B=(-)0.4A$		(-1.4)	(-2.0)	V
				0.9	2.0	V

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91098HA (KT)/90595MO (KOTO)/4017KI/1116MW, TS-3634/7039 No.679-1/4

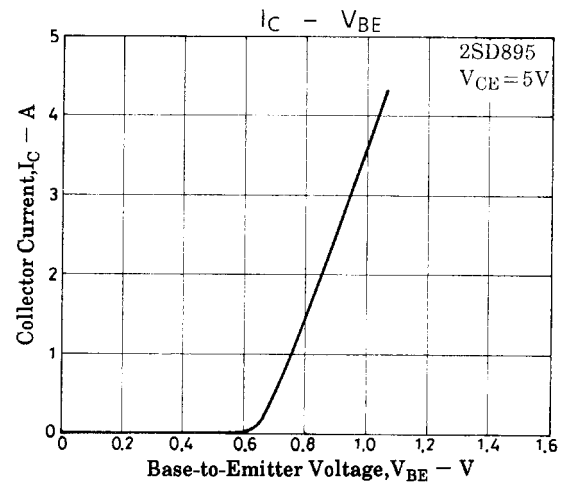
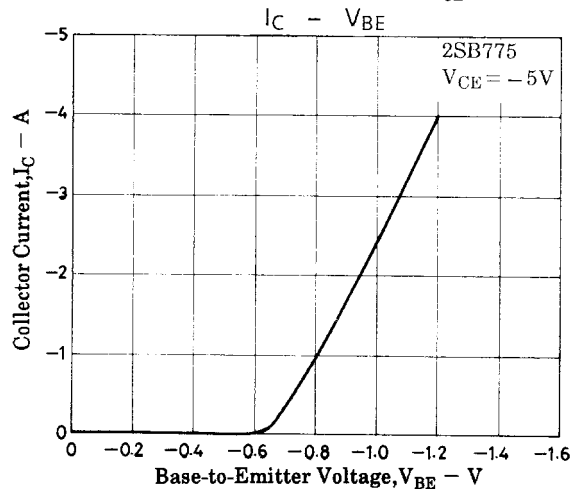
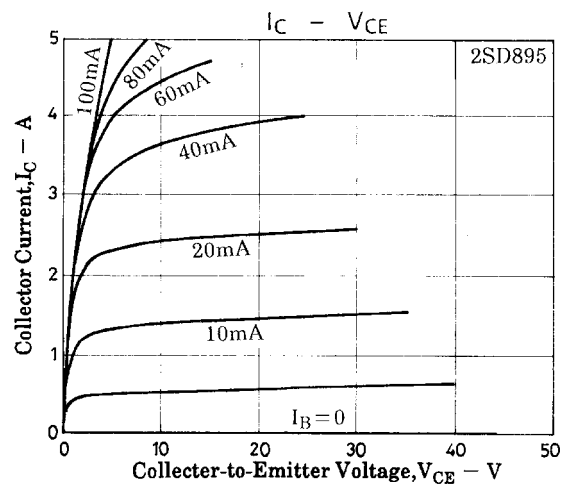
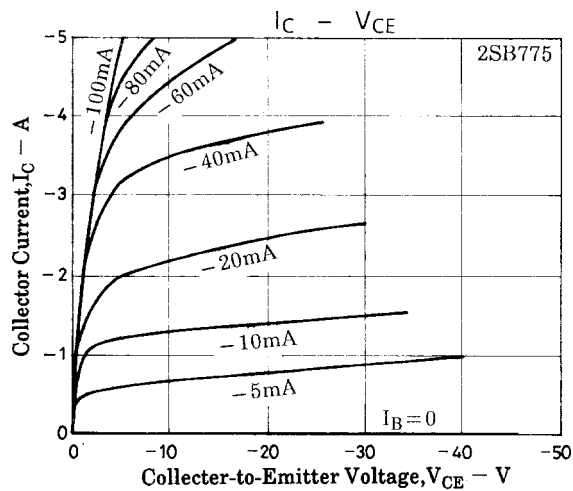
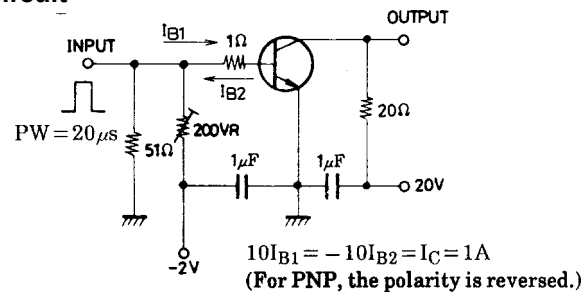
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)5mA, I_E = 0$	(-)100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)5mA, R_{BE} = \infty$	(-)85			V
		$I_C = (-)50mA, R_{BE} = \infty$	(-)85			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)5mA, I_C = 0$	(-)6			V
Turn-ON Time	t_{on}	See specified Test Circuit		(0.12)		μs
Storage Time	t_{stg}	See specified Test Circuit		0.20		μs
				(0.36)		μs
Fall Time	t_f	See specified Test Circuit		0.82		μs
				(1.29)		μs
				3.88		μs

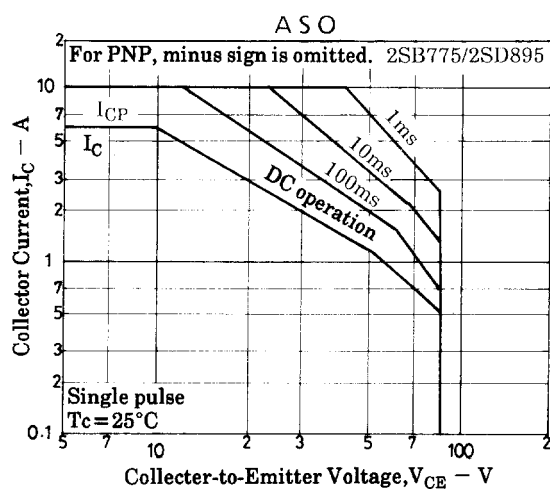
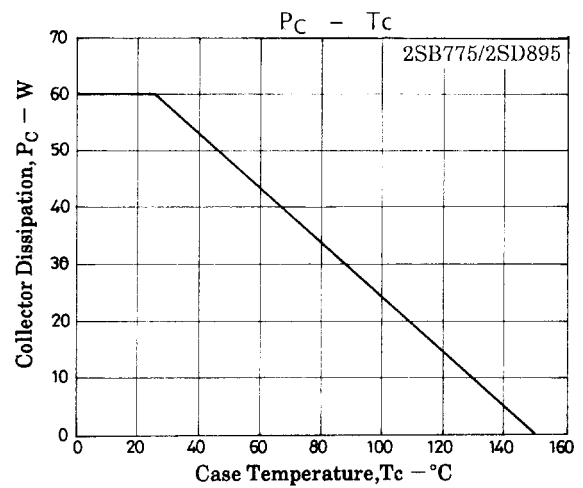
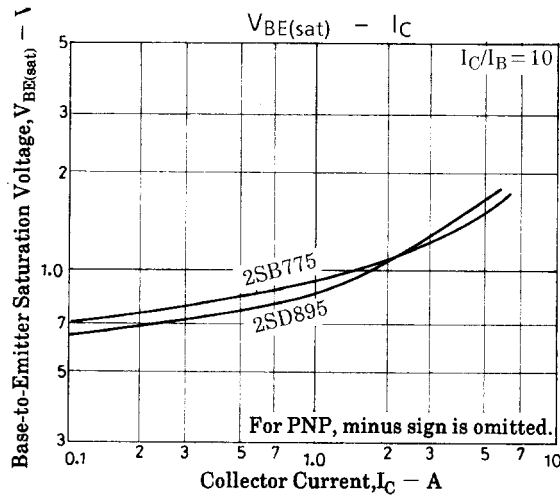
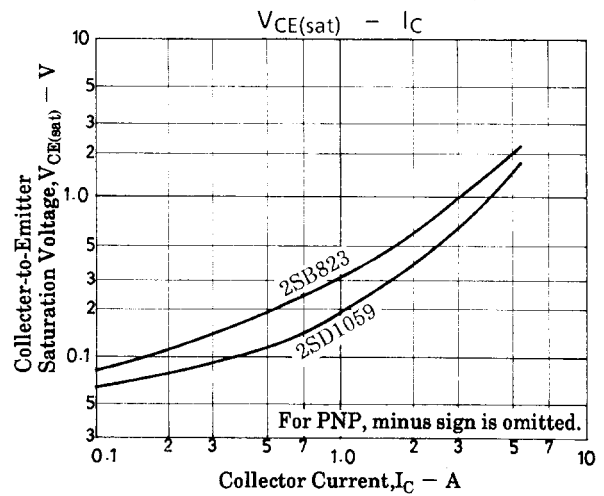
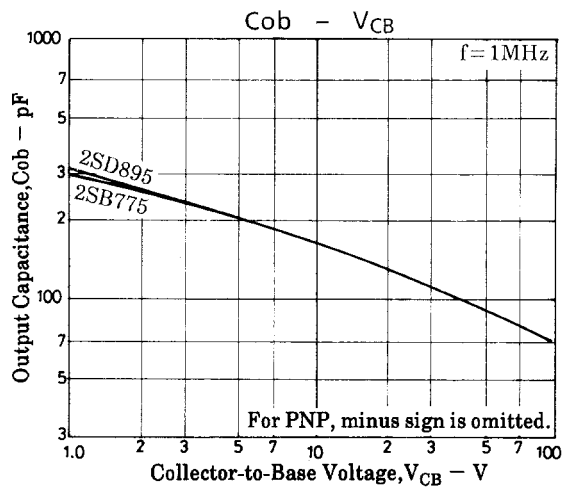
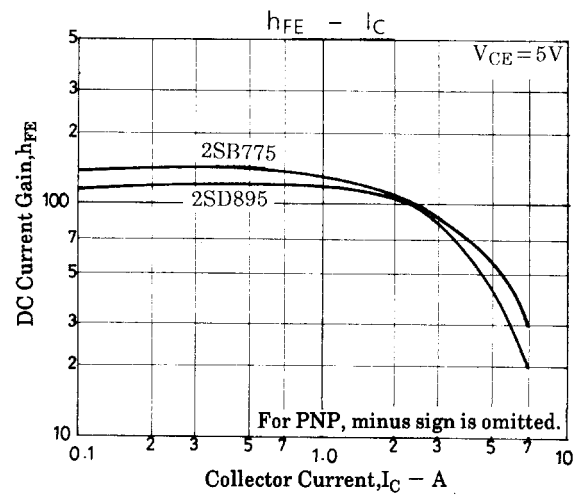
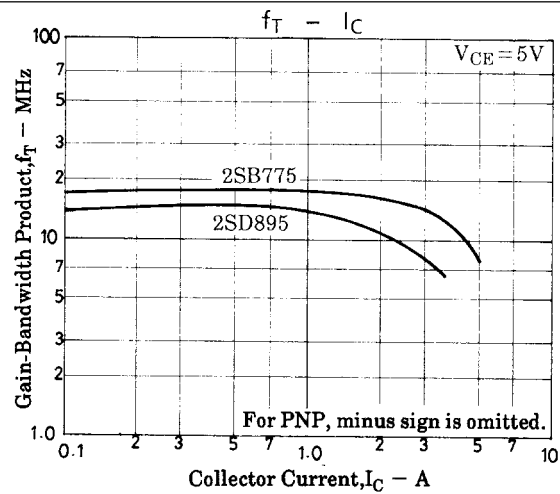
* : The 2SB775/2SD895 are classified by $1A h_{FE}$ as follows :

60	D	120	100	E	200
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Switching Time Test Circuit



2SB775/2SD895



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